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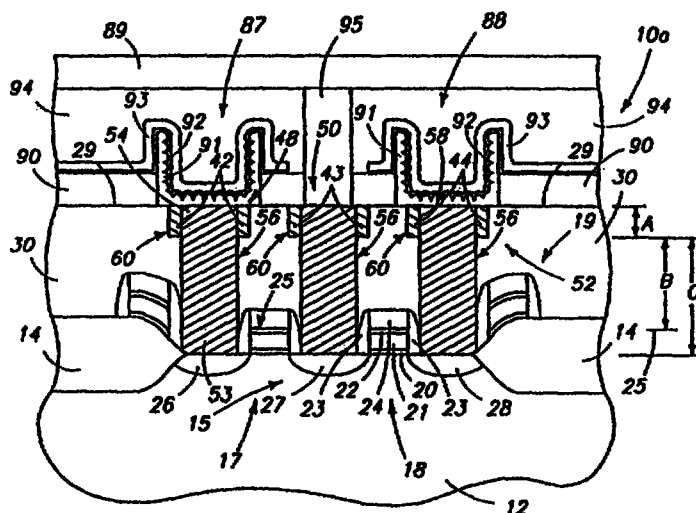
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(57) Abstract

A semiconductor processing method of forming a contact pedestal includes: a) providing a node location (28) to which electrical connection is to be made; b) providing insulating dielectric material (30) over the node location; c) etching a contact opening into the insulating dielectric material over the node location to a sufficient degree but not to outwardly expose the node location, the contact opening having a base; d) providing a spacer layer over the insulating dielectric material within the contact opening to a thickness which less than completely fills the contact opening; e) anisotropically etching the spacer layer to form a sidewall spacer (44) within the opening; f) etching through the contact opening base to outwardly expose the node location; g) filling the contact opening with an electrically conductive material (56); h) rendering the sidewall spacer electrically conductive.